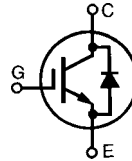


HiPerFAST™ IGBT Lightspeed™ Series

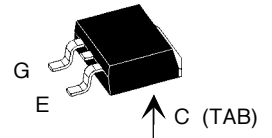
IXGA 12N60CD1
IXGP 12N60CD1

$V_{CES} = 600 \text{ V}$
 $I_{C25} = 24 \text{ A}$
 $V_{CE(sat)} = 2.7 \text{ V}$
 $t_{fi(typ)} = 55 \text{ ns}$

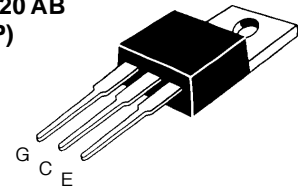


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	24	A
I_{C90}	$T_C = 90^\circ\text{C}$	12	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	48	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 33 \Omega, I_{CM} = 24 \text{ A}$ Clamped inductive load, $L = 300 \mu\text{H}$	@ $0.8 V_{CES}$	
P_C	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque with screw M3 Mounting torque with screw M3.5	0.45/4 0.55/5	Nm/lb.in.
Weight		4	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-263 (IXGA)



TO-220 AB (IXGP)



G = Gate C = Collector
E = Emitter TAB = Collector

Features

- Very high frequency IGBT
- New generation HDMOS™ process
- International standard package JEDEC TO-220AB and TO-263AA
- High peak current handling capability

Applications

- PFC circuit
- AC motor speed control
- DC servo and robot drives
- Switch-mode and resonant-mode power supplies
- High power audio amplifiers

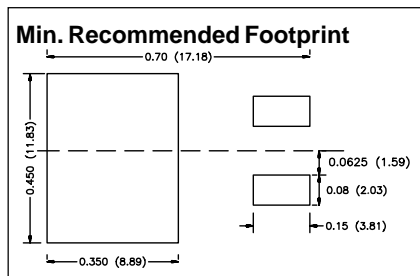
Advantages

- Fast switching speed
- High power density

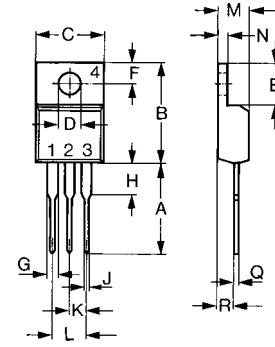
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{GE} = V_{CE}$	2.5		V
I_{CES}	$V_{CE} = 0.8 V_{CES}, V_{GE} = 0 \text{ V}$			200 μA 1.5 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{CE90}, V_{GE} = 15 \text{ V}$	2.1	2.7	V

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}, \text{ duty cycle} \leq 2\%$	5	11	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		860	pF
C_{oes}			100	pF
C_{res}			15	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5\ V_{CES}$		32	nC
Q_{ge}			10	nC
Q_{gc}			10	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 300\ \mu\text{H}$ $V_{CE} = 0.8\ V_{CES}, R_G = R_{off} = 18\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8\ V_{CES},$ higher T_J or increased R_G		20	ns
t_{ri}			20	ns
$t_{d(off)}$			60	ns
t_{fi}			55	ns
E_{off}			0.09	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 300\ \mu\text{H}$ $V_{CE} = 0.8\ V_{CES}, R_G = R_{off} = 18\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8\ V_{CES},$ higher T_J or increased R_G		20	ns
t_{ri}			20	ns
E_{on}			0.5	mJ
$t_{d(off)}$			85	180 ns
t_{fi}			85	180 ns
E_{off}		0.27	0.60 mJ	
R_{thJC}	IGBT			1.25 K/W
R_{thCK}		0.25		K/W

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
V_F	$I_F = 15\text{ A}; T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$		1.7	2.5 V
I_{RM}	$V_R = 100\text{ V}; I_F = 25\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}$ $L \leq 0.05\ \mu\text{H}; T_{VJ} = 100^\circ\text{C}$		2	2.5 A
t_{rr}	$I_F = 1\text{ A}; -di/dt = 50\text{ A}/\mu\text{s};$ $V_R = 30\text{ V}; T_J = 25^\circ\text{C}$		35	ns
R_{thJC}	Diode			1.6 K/W

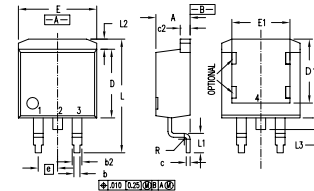


TO-220 AB (IXGP) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

TO-263 AA (IXGA) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025